

Configurable Multifunction Gate

NL7SZ58

The NL7SZ58 is an advanced high-speed CMOS multifunction gate. The device allows the user to choose logic functions AND, OR, NAND, NOR, XOR, INVERT and BUFFER.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.4 ns t_{PD} at $V_{CC} = 5$ V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 24 mA at 3.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

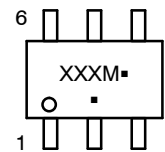
www.onsemi.com

MARKING DIAGRAMS



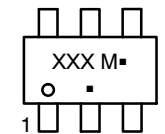
1

SC-88
CASE 419B-02



1

SC-74
CASE 318F-05



1

UDFN6, 1.45x1.0, 0.5P
CASE 517AQ



1

UDFN6, 1x1, 0.35P
CASE 517BX



XXX = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

NL7SZ58

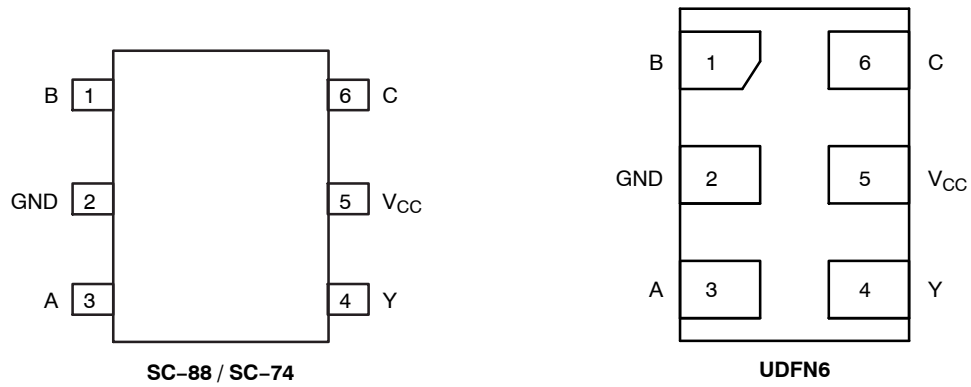


Figure 1. Pinout (Top View)

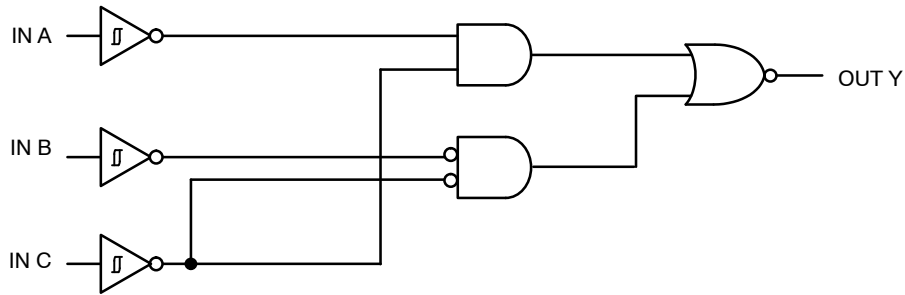


Figure 2. Function Diagram

PIN ASSIGNMENT

Pin	Function
1	B
2	GND
3	A
4	Y
5	V _{CC}
6	C

FUNCTION TABLE*

Input			Output
A	B	C	Y
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	L
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

*To select a logic function, please refer to "Logic Configurations section".

NL7SZ58

LOGIC CONFIGURATIONS

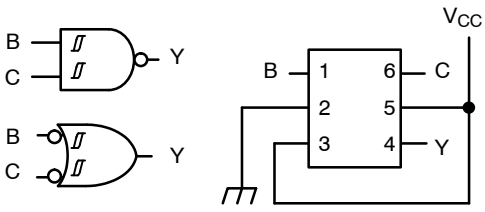


Figure 3. 2-Input NAND (When A = "H")

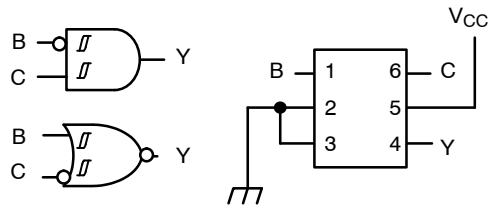


Figure 4. 2-Input AND with Input B Inverted (When A = "L")

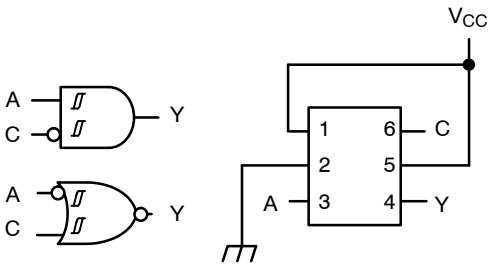


Figure 5. 2-Input AND with Input C Inverted (When B = "H")

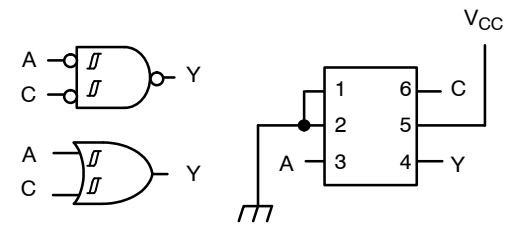


Figure 6. 2-Input OR (When B = "L")

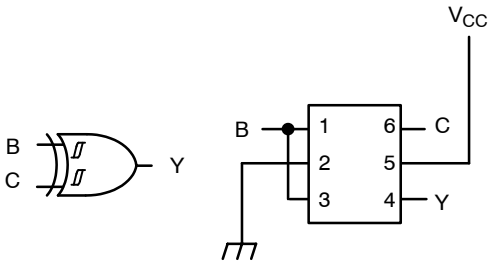


Figure 7. 2-Input XOR (When A = B)

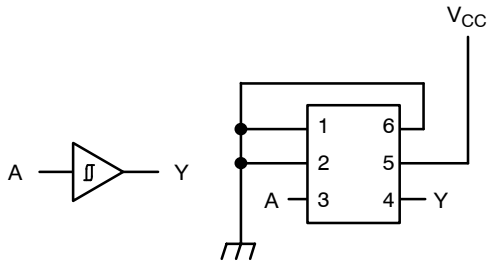


Figure 8. Buffer (When B = C = "L")

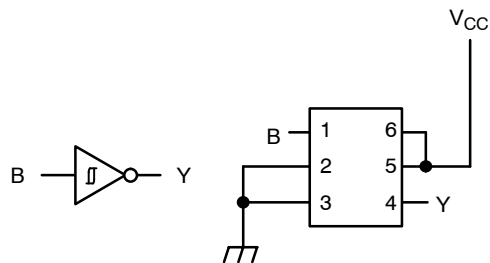


Figure 9. Inverter (When A = "L" and C = "H")

NL7SZ58

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V_{CC}	DC Supply Voltage SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V	
V_{IN}	DC Input Voltage SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V	
V_{OUT}	DC Output Voltage SC-88 (NLV) Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +7.0 -0.5 to +7.0	V	
	DC Output Voltage SC-88, SC-74, UDFN6 Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +6.5 -0.5 to +6.5	V	
I_{IK}	DC Input Diode Current $V_{IN} < GND$	-50	mA	
I_{OK}	DC Output Diode Current $V_{OUT} < GND$	-50	mA	
I_{OUT}	DC Output Source/Sink Current	± 50	mA	
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin	± 100	mA	
T_{STG}	Storage Temperature Range	-65 to +150	$^{\circ}C$	
T_L	Lead Temperature, 1 mm from Case for 10 Secs	260	$^{\circ}C$	
T_J	Junction Temperature Under Bias	+150	$^{\circ}C$	
θ_{JA}	Thermal Resistance (Note 2)	SC-88	659	$^{\circ}C/W$
		SC-74	555	
		UDFN6	382	
P_D	Power Dissipation in Still Air	SC-88	190	mW
		SC-74	225	
		UDFN6	327	
MSL	Moisture Sensitivity	Level 1		
F_R	Flammability Rating Oxygen Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in		
V_{ESD}	ESD Withstand Voltage (Note 3) Human Body Mode Charged Device Model (NLV) Charged Device Model	>2000	V	
		>200		
		N/A		
$I_{LATCHUP}$	Latchup Performance (Note 4) (NLV)	± 500 ± 100	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
3. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	Positive DC Supply Voltage	1.65	5.5	V
V_{IN}	DC Input Voltage	0	5.5	V
V_{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	0	5.5	V
T_A	Operating Free-Air Temperature	-55	+125	$^{\circ}C$
t_r, t_f	Input Rise or Fall Rate $V_{CC} = 1.65$ V to 1.95 V $V_{CC} = 2.3$ V to 2.7 V $V_{CC} = 3.0$ V to 3.6 V $V_{CC} = 4.5$ V to 5.5 V	0	No Limit	nS/V
		0	No Limit	
		0	No Limit	
		0	No Limit	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

NL7SZ58

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{T+}	Positive Input Threshold Voltage		1.65	-	-	1.4	-	1.4	-	1.4	V
			2.3	-	-	1.8	-	1.8	-	1.8	
			3.0	-	-	2.2	-	2.2	-	2.2	
			4.5	-	-	3.1	-	3.1	-	3.1	
			5.5	-	-	3.6	-	3.6	-	3.6	
V _{T-}	Negative Input Threshold Voltage		1.65	0.2	-	-	0.2	-	0.2	-	V
			2.3	0.4	-	-	0.4	-	0.4	-	
			3.0	0.6	-	-	0.6	-	0.6	-	
			4.5	1.0	-	-	1.0	-	1.0	-	
			5.5	1.2	-	-	1.2	-	1.2	-	
V _H	Input Hysteresis Voltage		1.65	0.1	0.48	0.9	0.1	0.9	0.1	0.9	V
			2.3	0.25	0.75	1.1	0.25	1.1	0.25	1.1	
			3	0.4	0.93	1.2	0.4	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	1.7	
V _{OH}	High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	1.65 to 5.5	V _{CC} - 0.1	V _{CC}	-	V _{CC} - 0.1	-	V _{CC} - 0.1	-	V
		I _{OH} = -4 mA	1.65	1.20	1.52	-	1.20	-	1.20	-	
		I _{OH} = -8 mA	2.3	1.9	2.1	-	1.9	-	1.9	-	
		I _{OH} = -16 mA	3	2.4	2.7	-	2.4	-	2.4	-	
		I _{OH} = -24 mA	3	2.3	2.5	-	2.3	-	2.3	-	
		I _{OH} = -32 mA	4.5	3.8	4	-	3.8	-	3.8	-	
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	-	0.1	V
		I _{OL} = 4 mA	1.65	-	0.08	0.45	-	0.45	-	0.45	
		I _{OL} = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.4	
		I _{OL} = 16 mA	3	-	0.28	0.4	-	0.4	-	0.5	
		I _{OL} = 24 mA	3	-	0.38	0.55	-	0.55	-	0.55	
		I _{OL} = 32 mA	4.5	-	0.42	0.55	-	0.55	-	0.65	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	+0.1	-	+1.0	-	+1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	-	10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	-	-	1.0	-	10	-	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NL7SZ58

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

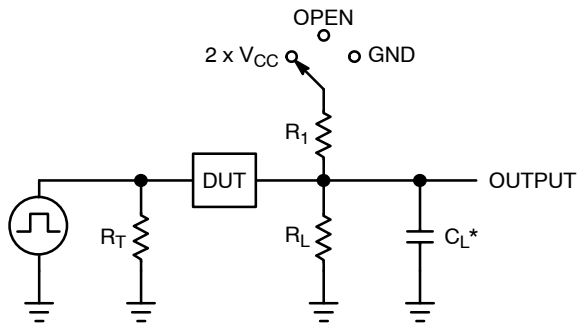
Symbol	Parameter	Condition	V_{CC} (V)	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$		$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH} , t_{PHL}	Propagation Delay (Figures 10 and 11)	$R_L = 1\text{ k}\Omega$, $C_L = 30\text{ pF}$	1.65 to 1.95	-	8.6	14.4	-	14.4	-	14.4	ns
		$R_L = 500\ \Omega$, $C_L = 30\text{ pF}$	2.3 to 2.7	-	5.1	8.3	-	8.3	-	8.3	
		$R_L = 500\ \Omega$, $C_L = 50\text{ pF}$	3.0 to 3.6	-	3.9	6.3	-	6.3	-	6.3	
			4.5 to 5.5	-	3.3	5.1	-	5.1	-	5.1	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	$V_{CC} = 5.5\text{ V}$, $V_{IN} = 0\text{ V}$ or V_{CC}	2.5	pF
C_{OUT}	Output Capacitance	$V_{CC} = 5.5\text{ V}$, $V_{IN} = 0\text{ V}$ or V_{CC}	4.0	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC} = 3.3\text{ V}$, $V_{IN} = 0\text{ V}$ or V_{CC} 10 MHz, $V_{CC} = 5.0\text{ V}$, $V_{IN} = 0\text{ V}$ or V_{CC}	16 19.5	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NL7SZ58



C_L includes probe and jig capacitance
 R_T is Z_{OUT} of pulse generator (typically 50 Ω)
 $f = 1$ MHz

Figure 10. Test Circuit

Test	Switch Position	C_L , pF	R_L , Ω	R_1 , Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$	50	500	500
t_{PHZ} / t_{PZH}	GND	50	500	500

X = Don't Care

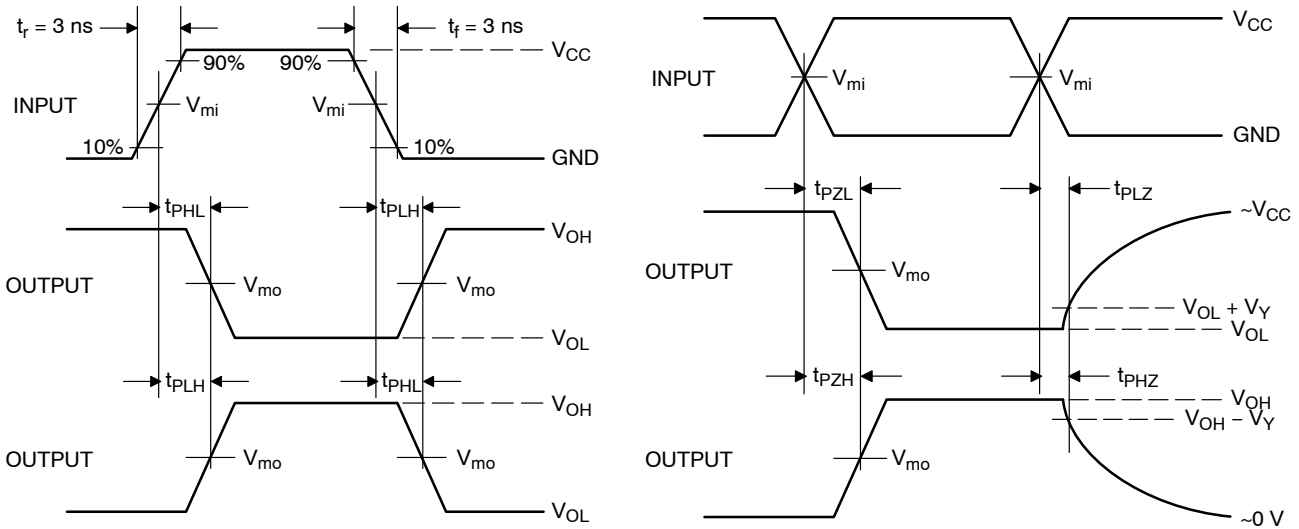


Figure 11. Switching Waveforms

V_{CC} , V	V_{mi} , V	V_{mo} , V		V_Y , V
		t_{PLH}, t_{PHL}	$t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}$	
1.65 to 1.95	$V_{CC} / 2$	$(V_{OH} - V_{OL}) / 2$	$V_{CC} / 2$	0.15
2.3 to 2.7	$V_{CC} / 2$	$(V_{OH} - V_{OL}) / 2$	$V_{CC} / 2$	0.15
3.0 to 3.6	$V_{CC} / 2$	$(V_{OH} - V_{OL}) / 2$	$V_{CC} / 2$	0.3
4.5 to 5.5	$V_{CC} / 2$	$(V_{OH} - V_{OL}) / 2$	$V_{CC} / 2$	0.3

NL7SZ58

ORDERING INFORMATION

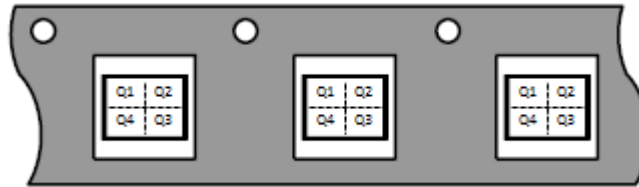
Device	Package	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL7SZ58DFT2G	SC-88 (Pb-Free)	MM	Q4	3000 / Tape & Reel
NLV7SZ58DFT2G*	SC-88 (Pb-Free)	MM	Q4	3000 / Tape & Reel
NL7SZ58DBVT1G	SC-74 (Pb-Free)	AM	Q4	3000 / Tape & Reel
NL7SZ58MU1TCG (In Development)	UDFN6, 1.45 x 1.0 x 0.35P (Pb-Free)	TBD	Q4	3000 / Tape & Reel
NL7SZ58MU3TCG (In Development)	UDFN6, 1.0 x 1.0 x 0.35P (Pb-Free)	TBD	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel

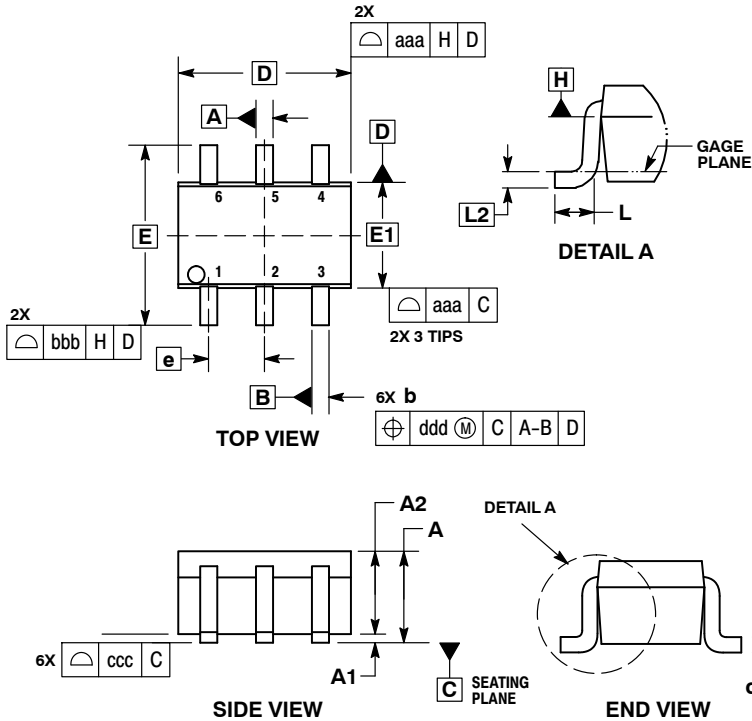
Direction of Feed



NL7SZ58

PACKAGE DIMENSIONS

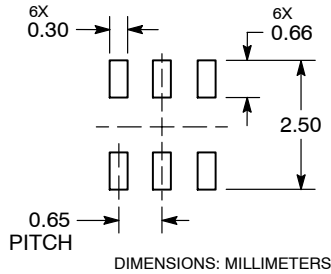
SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*

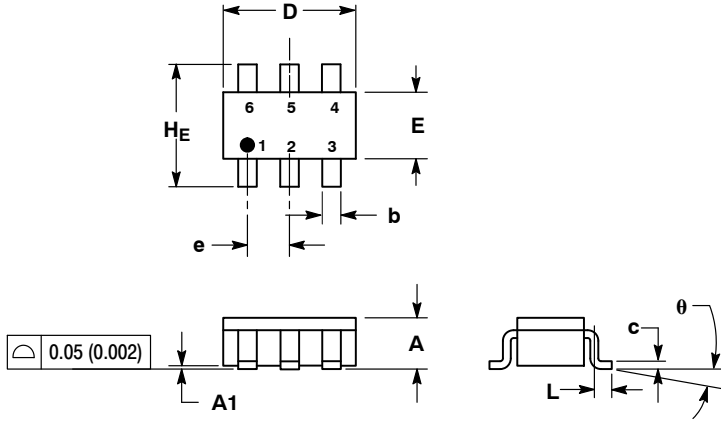


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NL7SZ58

PACKAGE DIMENSIONS

SC-74
CASE 318F-05
ISSUE N

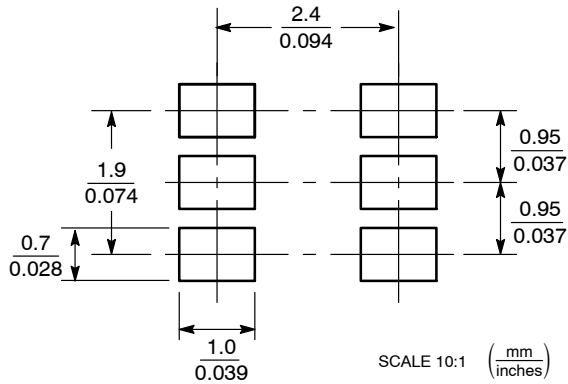


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.95	0.95	1.05	0.037	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ						

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. ANODE
- 6. CATHODE

STYLE 2:

- PIN 1. NO CONNECTION
- 2. COLLECTOR
- 3. EMITTER
- 4. NO CONNECTION
- 5. COLLECTOR
- 6. BASE

STYLE 3:

- PIN 1. EMITTER 1
- 2. BASE 1
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 2
- 6. COLLECTOR 1

STYLE 4:

- PIN 1. COLLECTOR 2
- 2. EMITTER 1/EMITTER 2
- 3. COLLECTOR 1
- 4. EMITTER 3
- 5. BASE 1/BASE 2/COLLECTOR 3
- 6. BASE 3

STYLE 5:

- PIN 1. CHANNEL 1
- 2. ANODE
- 3. CHANNEL 2
- 4. CHANNEL 3
- 5. CATHODE
- 6. CHANNEL 4

STYLE 6:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. CATHODE
- 6. CATHODE

STYLE 7:

- PIN 1. SOURCE 1
- 2. GATE 1
- 3. DRAIN 2
- 4. SOURCE 2
- 5. GATE 2
- 6. DRAIN 1

STYLE 8:

- PIN 1. EMITTER 1
- 2. BASE 2
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 1
- 6. COLLECTOR 1

STYLE 9:

- PIN 1. EMITTER 2
- 2. BASE 2
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 1
- 6. COLLECTOR 2

STYLE 10:

- PIN 1. ANODE/CATHODE
- 2. BASE
- 3. EMITTER
- 4. COLLECTOR
- 5. ANODE
- 6. CATHODE

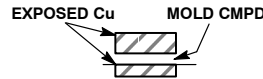
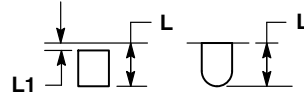
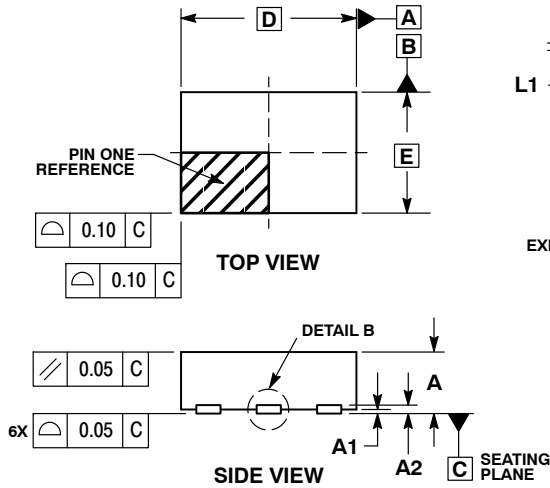
STYLE 11:

- PIN 1. EMITTER
- 2. BASE
- 3. ANODE/CATHODE
- 4. ANODE
- 5. CATHODE
- 6. COLLECTOR

NL7SZ58

PACKAGE DIMENSIONS

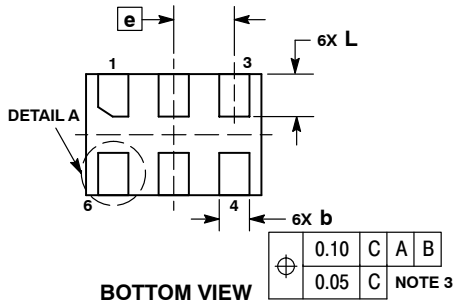
UDFN6, 1.45x1.0, 0.5P
CASE 517AQ
ISSUE O



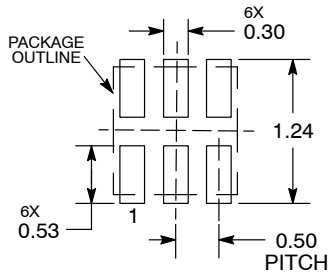
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07	REF
b	0.20	0.30
D	1.45	BSC
E	1.00	BSC
e	0.50	BSC
L	0.30	0.40
L1	---	0.15



MOUNTING FOOTPRINT



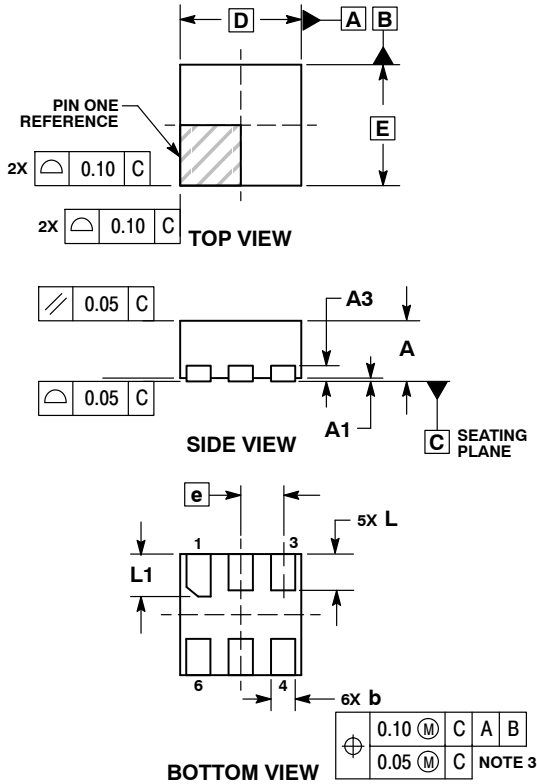
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NL7SZ58

PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P
CASE 517BX
ISSUE O

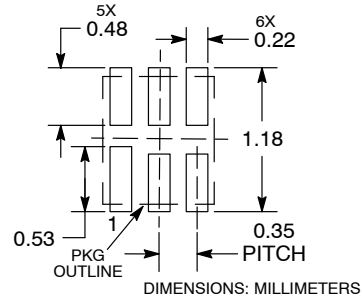


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.12	0.22
D	1.00	BSC
E	1.00	BSC
e	0.35	BSC
L	0.25	0.35
L1	0.30	0.40

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative